August 29（Tue.）

Session	Start time	Allotted time(min)	No.	Title	Speaker	Affiliation	Type
9. GaN/UWBG RF 2 Yohei Otoki Patrick Fay	8:30	25	9-1	Scaling of GaN HEMTs for microwave and millimeter-wave applications: achieving control of short-channel effects, deep levels and reliability	Enrico Zanoni	Univ. of Padova, Italy	invited
	8:55	25	9-2	Transport Properties in GaN under High Electric Field	Takuya Maeda	Univ. of Tokyo, Japan	invited
	9:20	15	9-3	>200 GHz fMAX MBE Grown AlScN/GaN High Electron Mobility Transistors	Kazuki Nomoto	Cornell University, USA	upgrade
	9:35	3	9-4	On the FET Drain-Source Capacitance Compensation Method forMicrowave GaN HEMT Class-E Power Amplifiers	Ritsuki Takahashi	Shibaura Inst. of Tech., Japan	sp
	9:38	3	9-5	Reliability Improvement of AlGaN/GaN HEMTs for Q-band and V-band Applications	Keiichi Matsushita	WIN Semiconductors Corp., Taiwan	sp
Coffee Break	9:45-10:05						
10. GaN Dielectric Interface Toshi-kazu Suzuki Enrico Zanoni	10:05	25	10-1	MOS interface control for GaN FETs and HEMTs	Tamotsu Hashizume	IMaSS, Nagoya Univ., Japan	invited
	10:30	25	10-2	Engineering of Interface Charges in AlSiO/AlN/p-type GaN-MOSFETs Toward Improvements of Threshold Voltage Stability and Channel Mobility	Tetsuo Narita	Toyota Central R&D Labs. Inc. /Nagoya Univ., Japan	invited
	10:55	3	10-3	Low-state-density Al2O3/n-GaN interfaces using mist chemical vapor deposited Al2O3 gate insulator	Zenji Yatabe	Kumamoto Univ./Hokkaido Univ., Japan	sp
	10:58	3	10-4	Improved device performance in in-situ SiN/AlN/GaN MIS-HEMTs with ex-situ HfO2 and Al2O3 passivation by atomic layer deposition	Pradip Dalapati	Nanyang Tech. Univ., Singapore	sp
	11:01	3	10-5	Impact of post metallization annealing in EID AlGaN/GaN MOS-HEMTs	Takuma Nanjo	Mitsubishi Electric Corp./Saga Univ./Nagoya Inst. of Tech., Japan	sp
	11:04	3	10-6	Study on Effects of Mechanical Stress in Normally-off EID AlGaN/GaN MOS-HEMTs by TCAD Simulation	Toshiyuki Oishi	Saga Univ./Mitsubishi Electric Corp., Japan	sp
11. Poster Viewing 2	11:10-12:10			No. 7-4, 8-3, 8-4, 8-5, 8-6, 8-7, 8-8, 9-4, 9-5, 10-3, 10-4, 10-5, 10-6, 12-4, 12-5			
Lunch	12:10-13:30						
12. Emerging Materials & Devices Naoteru Shigekawa Toshiyuki Oishi	13:30	25	12-1	Textured Solar Arrays for Stratospheric UAV	Noren Pan	Microlink Devices Inc., USA	invited
	13:55	25	12-2	Large-Area Ultra-Heavy Boron-Doped Diamond Films: Advanced Sensing Material for Electrochemical Fingerprinting	Shinya Ohmagari	AIST, Japan	invited
	14:20	25	12-3	Wafer-Scale Heterogeneous Integration of Functional Materials for High-Performance Power, Photonic and RF Devices	Xin Ou	SIMIT, Chinese Academy of Sci., China	invited
	14:45	3	12-4	Wafer-scale single-crystalline GaN-based heterogeneous integration material by ion-cutting technique	Tiangui You	SIMIT, Chinese Academy of Sci., China	sp
	14:48	3	12-5	Effect of external stimulation on 1/ƒ dynamics in 2D cellular automaton	Hazumi Ueda	Hokkaido Univ., Japan	sp
Closing	14:55	15					